

Silicon NPN Power Transistors

2SC4370

**DESCRIPTION**

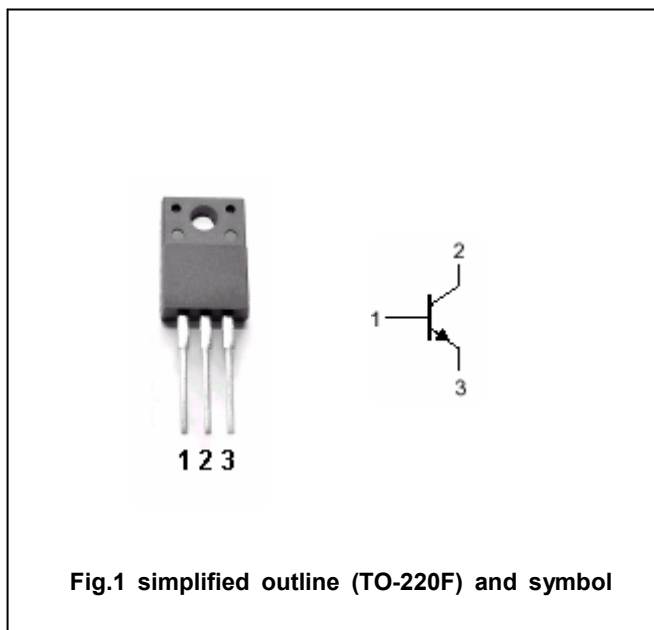
- With TO-220F package
- Complement to type 2SA1659
- High transition frequency

**APPLICATIONS**

- High voltage applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



**Absolute maximum ratings (Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	160	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	160	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		1.5	A
I <sub>B</sub>	Base current		0.15	A
P <sub>C</sub>	Collector dissipation	T <sub>C</sub> =25°C	20	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA ; I <sub>B</sub> =0	160			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =0.5A; I <sub>B</sub> =50mA			1.5	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =0.5A; V <sub>CE</sub> =5V			1.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =160V; I <sub>E</sub> =0			1.0	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			1.0	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =5V	70		240	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =10V		100		MHz
C <sub>OB</sub>	Collector output capacitance	f=1MHz; V <sub>CB</sub> =10V		25		pF

◆ h<sub>FE</sub> Classifications

O	Y
70-140	120-240

